

MBR2H200SFT3G

Surface Mount Schottky Power Rectifier

Plastic SOD-123FL Package

This device uses the Schottky Barrier principle with a large area metal-to-silicon power diode. Ideally suited for low voltage, high frequency rectification or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC-DC and DC-DC converters, reverse battery protection, and “Oring” of multiple supply voltages and any other application where performance and size are critical.

Features

- Guardring for Stress Protection
- Low Forward Voltage
- Epoxy Meets UL 94 V-0
- Package Designed for Optimal Automated Board Assembly
- These are Pb-Free Devices

Mechanical Characteristics

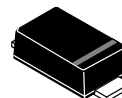
- Reel Options: MBR2H200SFT3G = 10,000 per 13 in reel/8 mm tape
- Device Marking: L2J
- Polarity Designator: Cathode Band
- Weight: 11.7 mg (approximately)
- Case: Epoxy, Molded
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements



ON Semiconductor®

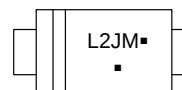
<http://onsemi.com>

**SCHOTTKY BARRIER
RECTIFIER
2.0 AMPERES
200 VOLTS**



**SOD-123FL
CASE 498**

MARKING DIAGRAM



L2J = Specific Device Code
M = Date Code
■ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MBR2H200SFT3G	SOD-123 (Pb-Free)	10000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MBR2H200SFT3G

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	V
Average Rectified Forward Current ($T_L = 108^\circ\text{C}$)	I_O	2.0	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz, $T_C = 105^\circ\text{C}$)	I_{FRM}	4.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	30	A
Storage and Operating Junction Temperature Range (Note 1)	T_{stg}, T_J	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Note 2)	Ψ_{JCL}	23	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	85	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{\theta JA}$	330	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 4) ($I_F = 1.0\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 2.0\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 1.0\text{ A}$, $T_J = 125^\circ\text{C}$) ($I_F = 2.0\text{ A}$, $T_J = 125^\circ\text{C}$)	V_F	0.86 0.94 0.71 0.78	V
Maximum Instantaneous Reverse Current (Note 4) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$)	I_R	200 2	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Mounted with 700 mm² copper pad size (Approximately 1 in²) 1 oz FR4 Board.
3. Mounted with pad size approximately 20 mm² copper, 1 oz FR4 Board.
4. Pulse Test: Pulse Width $\leq 380\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

TYPICAL CHARACTERISTICS

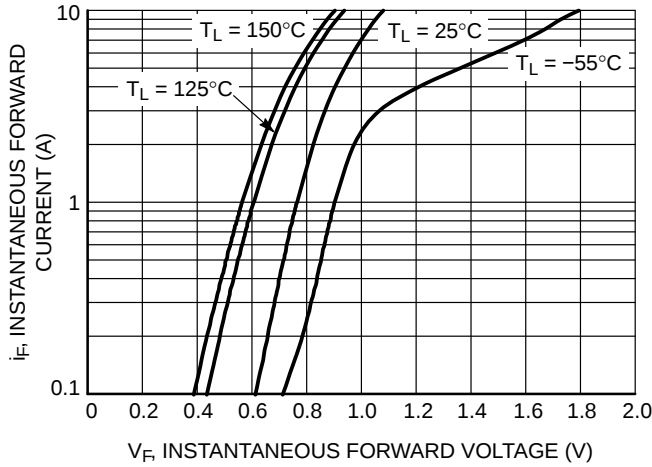


Figure 1. Typical Instantaneous Forward Characteristics

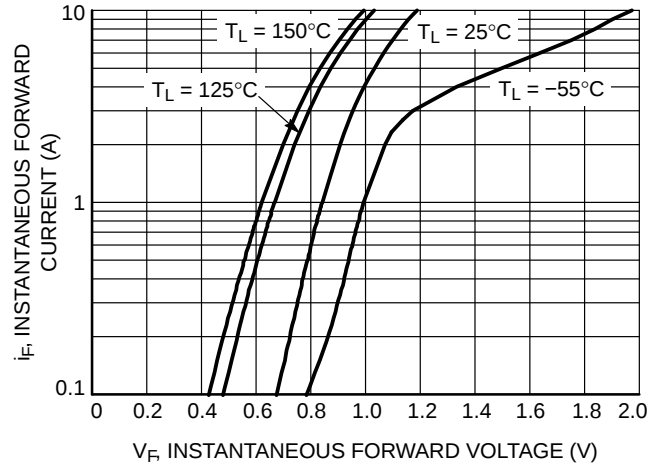


Figure 2. Maximum Instantaneous Forward Characteristics

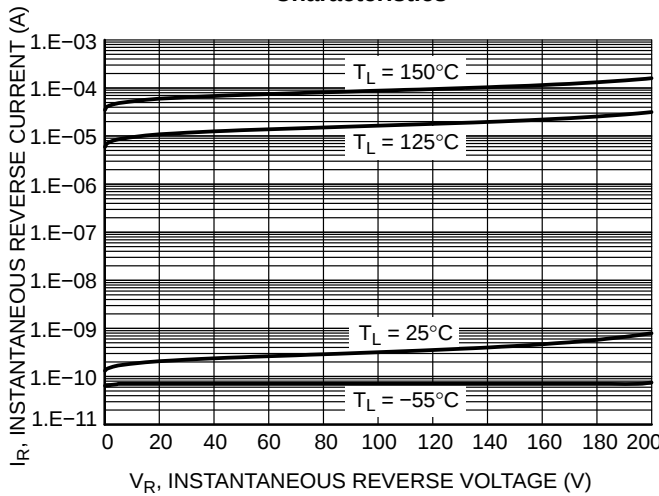


Figure 3. Typical Reverse Characteristics

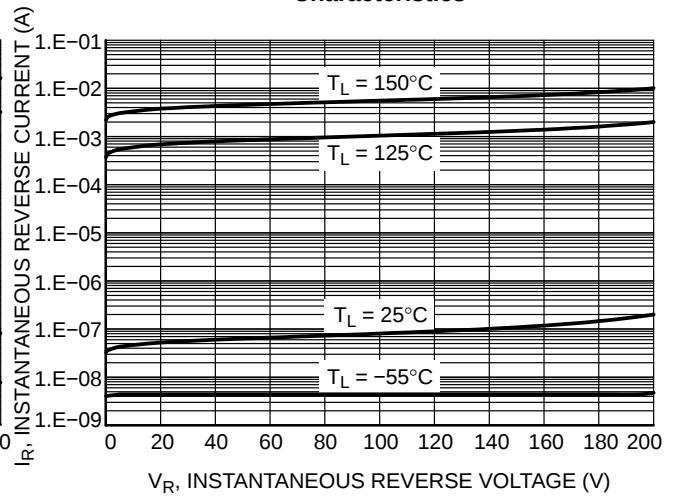


Figure 4. Maximum Reverse Characteristics

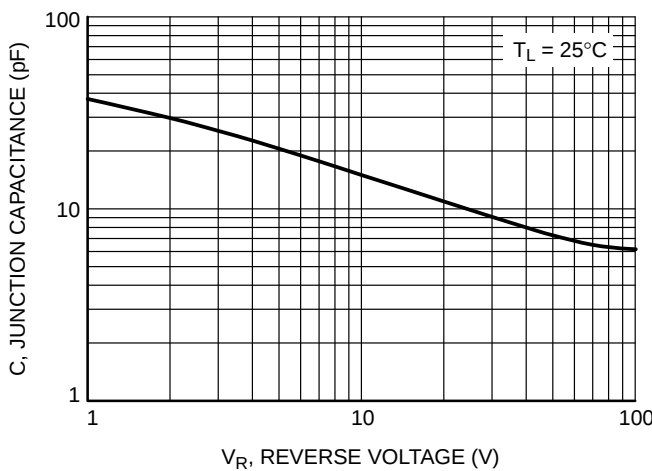


Figure 5. Typical Junction Capacitance

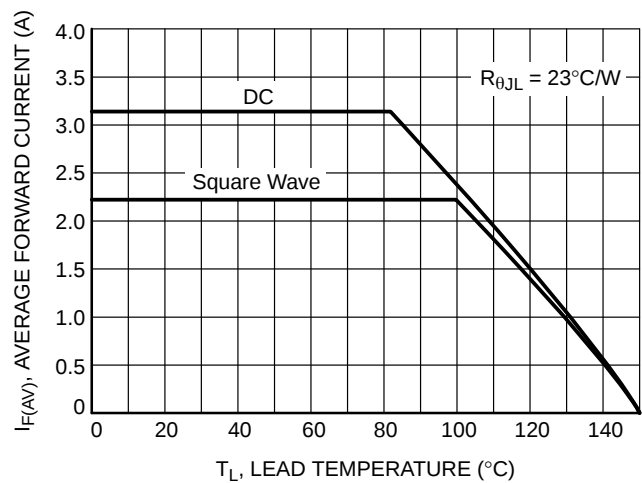


Figure 6. Current Derating per Diode

MBR2H200SFT3G

TYPICAL CHARACTERISTICS

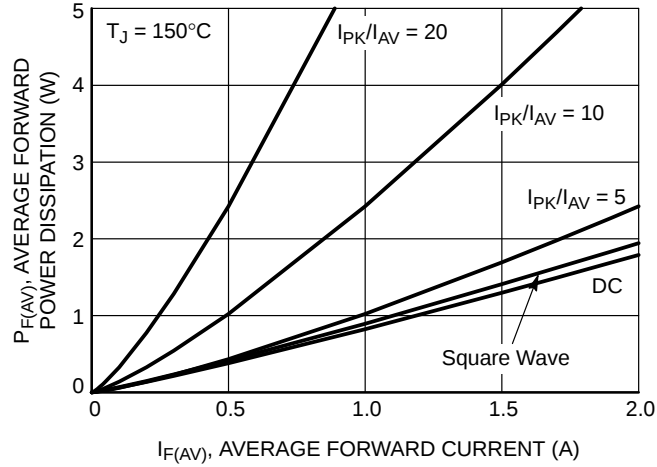


Figure 7. Forward Power Dissipation

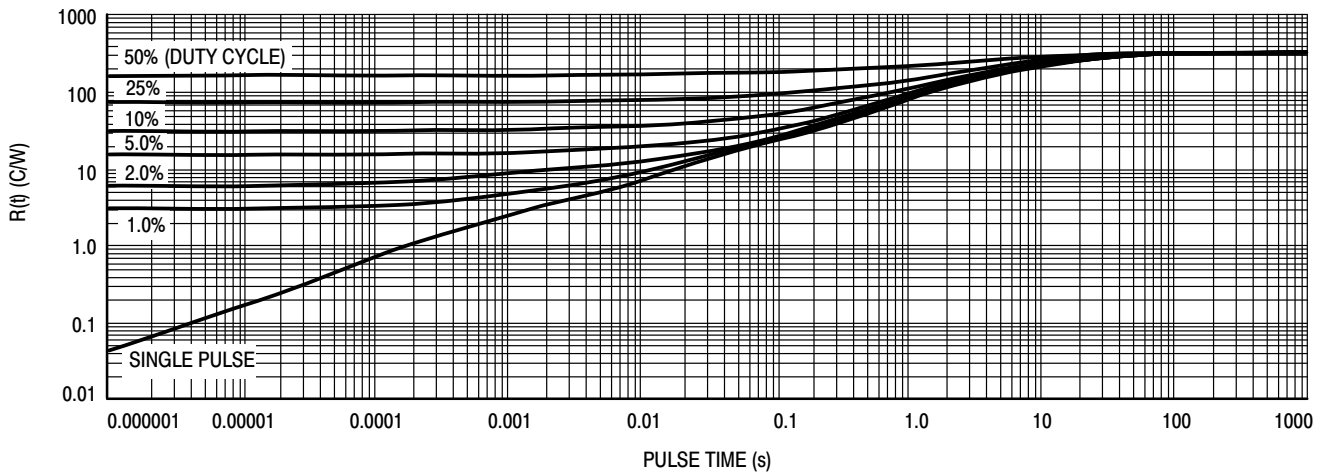


Figure 8. Thermal Response, Junction-to-Ambient (20 mm² pad)

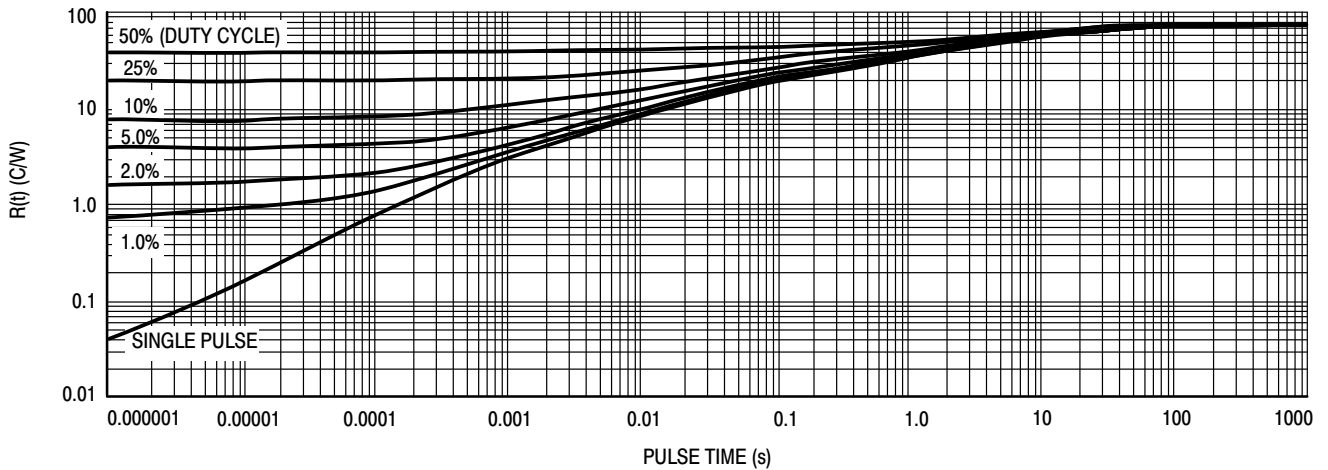
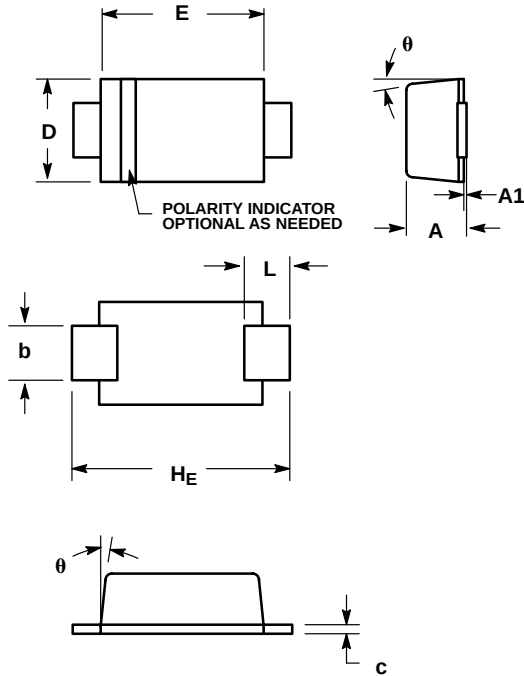


Figure 9. Thermal Response, Junction-to-Ambient (1 in² pad)

MBR2H200SFT3G

PACKAGE DIMENSIONS

SOD-123FL
CASE 498
ISSUE B

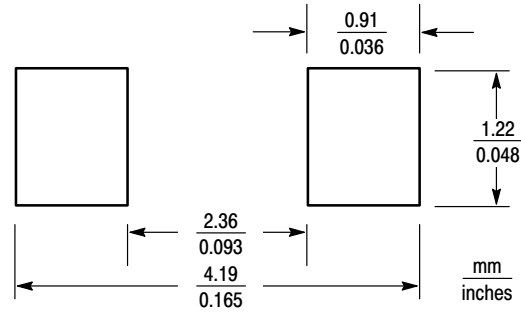


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH.
4. DIMENSIONS D AND J ARE TO BE MEASURED ON FLAT SECTION OF THE LEAD: BETWEEN 0.10 AND 0.25 MM FROM THE LEAD TIP.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	0.95	1.00	0.035	0.037	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.70	0.90	1.10	0.028	0.035	0.043
c	0.10	0.15	0.20	0.004	0.006	0.008
D	1.50	1.65	1.80	0.059	0.065	0.071
E	2.50	2.70	2.90	0.098	0.106	0.114
L	0.55	0.75	0.95	0.022	0.030	0.037
H _E	3.40	3.60	3.80	0.134	0.142	0.150
θ	0°	—	8°	0°	—	8°

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9